

SPECIFICATION OF LED CHIP

C1330-30

[NIR]

1) Commodity Type and Physical Characteristics.

- | | | | |
|----------------------|------------------|------------------|------------|
| 1. Material | InGaAsP/InP(DDH) | | |
| 2. Electrode | Top Side | P (anode) side | : Au Alloy |
| | Bottom Side | N (cathode) side | : Au Alloy |
| 3. Electrode Pattern | Fig.1 | | |
| 4. Chip Size | Fig.2 | | |
| 5. Chip Thickness | Fig.2 | | |
| 6. Emission Area | Fig.2 | | |

2) Electro-Optical Characteristics [Ta=25°C]

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		0.9	1.2	V
		If=50mA		1.0	1.3	
Reverse Current	Ir	Vr=3V			10	uA
Power Intensity	Po	If=20mA		1.5		mW
		If=50mA		3.0		
Peak Wavelength	λ_P	If=20mA		1330		nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		90		nm
RiseTime	tr	If=20mA		25		ns
FallTime	tf	If=20mA		20		ns

‡ Die shall be mounted on TO-18 gold header without resin coated.

‡ Power intensity is measured by PD G8370-85.

[Unit: um]

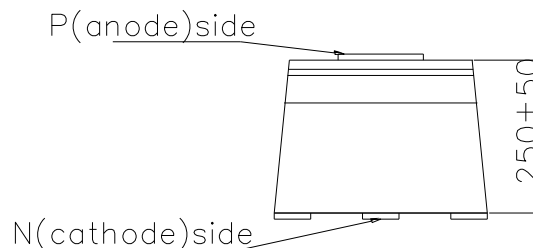
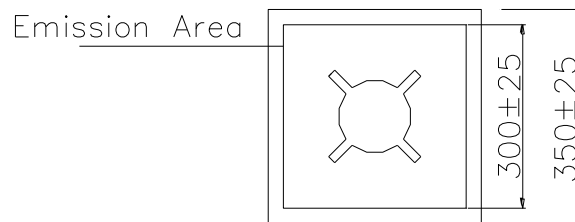
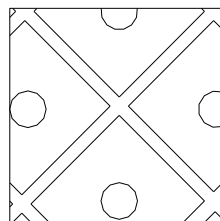
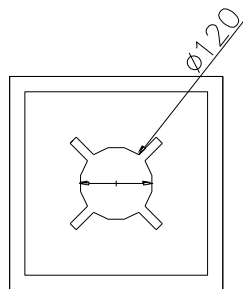


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area